S J C Irvine

List of Publications by Year
in descending order

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48 papers	1,175 citations	516215 16 h-index	377514 34 g-index
48 all docs	48 docs citations	48 times ranked	1009 citing authors

#	Article	IF	Citations
1	Data on dopant characteristics and band alignment of CdTe cells with and without a ZnO highly-resistive-transparent buffer layer. Data in Brief, 2019, 22, 218-221.	0.5	4
2	Comparative study of conventional vs. one-step-interconnected (OSI) monolithic CdTe modules. Materials Research Innovations, 2015, 19, 488-493.	1.0	2
3	Chemical analysis of Cd_{1âˆ'x}Zn_xS/CdTe solar cells by plasma profiling TOFMS. Materials Research Innovations, 2014, 18, 82-85.	1.0	10
4	Investigation into ultrathin CdTe solar cell Voc using SCAPS modelling. Materials Research Innovations, 2014, 18, 505-508.	1.0	5
5	CdCl2 treatment related diffusion phenomena in Cd1âˆ'xZnxS/CdTe solar cells. Journal of Applied Physics, 2014, 115, .	1.1	16
6	Developing Monolithically Integrated CdTe Devices Deposited by AP-MOCVD. Materials Research Society Symposia Proceedings, 2013, 1538, 275-280.	0.1	0
7	Impedance spectroscopy of thin-film CdTe/CdS solar cells under varied illumination. Journal of Applied Physics, 2009, 106, .	1.1	68
8	The application of a statistical methodology to investigate deposition parameters in CdTe/CdS solar cells grown by MOCVD. Journal of Materials Science: Materials in Electronics, 2008, 19, 639-645.	1.1	3
9	Comparative study of trap densities of states in CdTeâˆ•CdS solar cells. Applied Physics Letters, 2007, 91, 153505.	1.5	14
10	Grain and crystal texture properties of absorber layers in MOCVD-grown CdTe/CdS solar cells. Semiconductor Science and Technology, 2006, 21, 763-770.	1.0	65
11	MOCVD of highly conductive CdO thin films. Journal of Materials Science: Materials in Electronics, 2004, 15, 369-372.	1.1	25
12	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 559-566.	1.1	10
13	Photochemical Vapour Deposition of Thin Films. , 2002, , 199-222.		0
14	Experimental Confirmation of the Predicted Shallow Donor Hydrogen State in Zinc Oxide. Physical Review Letters, 2001, 86, 2601-2604.	2.9	415
15	1,1-Dimethylhydrazine as a high purity nitrogen source for MOVPE-water reduction and quantification using nuclear magnetic resonance, gas chromatography-atomic emission detection spectroscopy and cryogenic-mass spectroscopy analytical techniques. Journal of Electronic Materials, 2000, 29, 161-164.	1.0	12
16	In-situ post annealing treatment of nitrogen-doped ZnSe grown using photo-assisted MOVPE. Journal of Electronic Materials, 2000, 29, 169-172.	1.0	4
17	Reduction of threading dislocation density in GaN using an intermediate temperature interlayer. Applied Physics Letters, 2000, 77, 3562-3564.	1.5	30
18	Importance of initial nucleation step on low temperature photoassisted MOVPE growth of ZnSe. Journal of Materials Science: Materials in Electronics, 1999, 10, 595-600.	1.1	2

#	Article	IF	Citations
19	Insights into MOCVD process control as revealed by laser interferometry. Journal of Electronic Materials, 1999, 28, 712-717.	1.0	4
20	Title is missing!. Journal of Materials Science: Materials in Electronics, 1998, 9, 211-216.	1.1	5
21	The kinetics of the growth of nitrogen-doped ZnSe grown by photo-assisted MOVPE. Journal of Electronic Materials, 1998, 27, 763-768.	1.0	9
22	The use ofin situlaser interferometry for MOCVD process control. Semiconductor Science and Technology, 1998, 13, 1407-1411.	1.0	24
23	Variation of the effective extinction coefficient during pyrolytic and photo-assisted II-VI MOVPE growth, measured by in situ laser interferometry. Semiconductor Science and Technology, 1998, 13, 1412-1417.	1.0	5
24	New mechanisms in photo-assisted MOVPE of II-VI semiconductors. Journal of Electronic Materials, 1997, 26, 723-727.	1.0	11
25	Metal-organic vapour phase epitaxy. , 1997, , 71-96.		10
26	Dynamic vapor pressure measurements of the dimethyl zinc.triethylamine adduct using an ultrasonic monitor. Applied Physics Letters, 1996, 68, 1294-1296.	1.5	17
27	MOCVD-grown wider-bandgap capping layers in long-wavelength infrared photoconductors. Semiconductor Science and Technology, 1996, 11, 1912-1922.	1.0	18
28	IntegratedIn Situ wafer and system monitoring for the growth of CdTe/ZnTe/GaAs/Si for mercury cadmium telluride epitaxy. Journal of Electronic Materials, 1995, 24, 457-465.	1.0	15
29	P-type doping of double layer mercury cadmium telluride for junction formation. Journal of Electronic Materials, 1995, 24, 617-624.	1.0	7
30	Integrated in situ monitoring of a metalorganic vapor phase epitaxy reactor for IIâ€“VI epitaxy. Journal of Electronic Materials, 1994, 23, 167-173.	1.0	11
31	A new N-type doping precursor for MOCVD-IMP growth of detector quality MCT. Journal of Electronic Materials, 1993, 22, 859-864.	1.0	16
32	Modeling of in situ monitored laser reflectance during MOCVD growth of HgCdTe. Journal of Electronic Materials, 1993, 22, 899-906.	1.0	30
33	In situ characterization techniques for monitoring and control of VPE growth of Hg1-xCdxTe. Semiconductor Science and Technology, 1993, 8, 860-871.	1.0	14
34	Infrared photoluminescence characterization of long-wavelength HgCdTe detector materials. Semiconductor Science and Technology, 1993, 8, 941-945.	1.0	14
35	As diffusion in Hg1-xCdxTe for junction formation. Semiconductor Science and Technology, 1993, 8, S270-S275.	1.0	24
36	Spatially resolved characterization of HgCdTe materials and devices by scanning laser microscopy. Semiconductor Science and Technology, 1993, 8, 872-887.	1.0	36

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37	Study of microinhomogeneities in midwave infrared mercury cadmium telluride grown by metalorganic chemical vapor deposition-interdiffused multilayer process onto GaAs and GaAs/Si substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1392.	1.6	17
38	MOVPE growth of HgCdTe. Semiconductor Science and Technology, 1991, 6, C15-C21.	1.0	16
39	Laserâ€induced selected area epitaxy of CdTe and HgTe. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1059-1066.	0.9	16
40	Selected area epitaxy in IIâ€“VI compounds by laser-induced photo-metalorganic vapor phase epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 1191.	1.6	13
41	A study of the structure and electrical properties of CdxHg1â^'xTe grown by metalorganic vapor phase epitaxy (interdiffused multilayer process). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1989, 7, 285-290.	0.9	41
42	Mechanisms in the Photochemical Growth of Cadmium Mercury Telluride. NATO ASI Series Series B: Physics, 1989, , 243-252.	0.2	0
43	Orientation Effects on the Heteroepitaxial Growth of Cd_xH_{g1â^'x}Te on to CdTe and GaAs. Materials Research Society Symposia Proceedings, 1986, 90, 389.	0.1	22
44	Interdiffused Multilayer Processing (IMP) in Alloy Growth. Materials Research Society Symposia Proceedings, 1986, 90, 367.	0.1	7
45	A Study of UV Absorption Spectra and Photolysis of Some Group II and Group VI Alkyls. Journal of the Electrochemical Society, 1985, 132, 968-972.	1.3	28
46	Low Temperature Growth of HgTe by a UV Photosensitisation Method. Springer Series in Chemical Physics, 1984, , 234-238.	0.2	3
47	Uv Absorption Spectra and Photolysis of Some Group II and Group VI Alkyls. Materials Research Society Symposia Proceedings, 1983, 29, 253.	0.1	5
48	The growth of CdxHg1â^'xTe using organometallics. Journal of Vacuum Science and Technology, 1982, 21, 178-181.	1.9	52